

High Power AlGaInP Laser Diode

Overview

DL-4038-021 is a high power 635 nm (Typ.) AlGaInP laser diode with low threshold current. High output power and low threshold current are achieved by use of a strained quantum well active layer. The lasing wavelength is the same as that of the He-Ne gas lasers. DL-4038-021 is suitable for applications such as laser printers, line markers and other optical information systems.

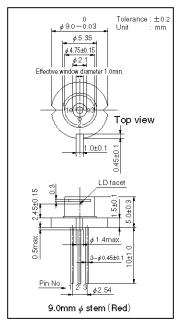
Features

Short wavelength : 635 nm (Typ.)
High output power : 10mW CW
Low threshold current : Ith = 35 mA (Typ.)
Low operating voltage : Vop = 2.2 V (Typ.)

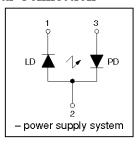
Absolute Maximum Ratings at Tc=25℃

Parameter		Symbol	Ratings	Unit	
Light Output		Po	10	mW	
Reverse Voltage	Laser PIN	Vr	2 30	V	
Operating Temperature		Topr	-10 to +40	$^{\circ}\mathbb{C}$	
Storage Temperature		Tstg	-40 to +85	$^{\circ}\mathbb{C}$	

Package Dimensions



Electrical Connection



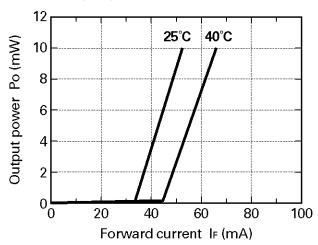
Electrical and Optical Characteristics at Tc=25°C

Para	meter	Symbol	Condition	Min.	Тур.	Max.	Unit
Threshol	d Current	Ith	CW	-	35	60	mA
Operating	g Current	Iop	Po=10mW	_	55	80	mA
Operatin	g Voltage	Vop	Po=10mW	_	2.2	2.4	V
Lasing W	avelength	λp	Po=10mW	_	635	645	nm
Beam 💥)	Perpendicular	$\theta \perp$	Po=10mW	25	30	35	deg.
Divergence	Parallel	θ //	Po=10mW	6	8	10	deg.
Off Axis	Perpendicular	$\Delta \theta \perp$	-	_	-	±3	deg.
Angle	Parallel	$\Delta heta$ //	_	_	_	±3	deg.
Differentia	Efficiency	dPo/dIop	_	_	0.5	_	mW/mA
Monitoring C	utput Current	Im	Po=10mW	0.05	0.15	0.4	mA
Astign	natism	As	Po=10mW	_	8	_	μm

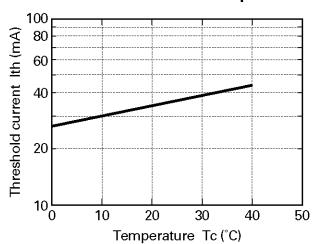
💥) Full angle at half maximum note: The above product specifications are subject to change without notice.

Characteristics

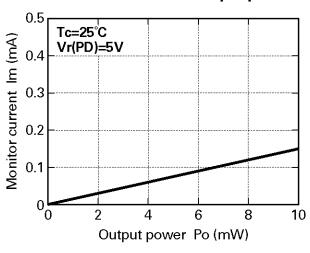




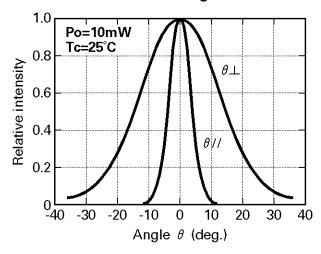
Threshold current vs. Temperature



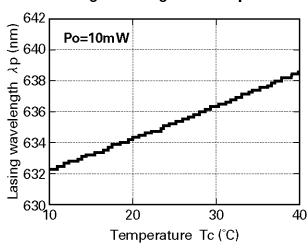
Monitor current vs. Output power



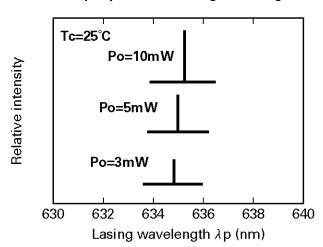
Beam divergence



Lasing wavelength vs. Temperature



Output power vs. Lasing wavelength





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Precautionary instructions in handling gallium arsenic products

Special precautions must be taken in handling this product because it contains, gallium arsenic, which is designated as a toxic substance by law. Be sure to adhere strictly to all applicable laws and regulations enacted for this substance, particularly when it comes to disposal.

Manufactured by; Tottori SANYO Electric Co., Ltd.

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